

## TPS92561 – 针对发光二极管 (LED) 照明的相位可调光、单级升压控制器

### 特性

- 简单滞后控制
- 紧凑解决方案和简单物料清单
- 自然可调光三端双向可控硅 (TRIAC) 和反相位调光器
- 执行 LED 驱动电路，此电路效率大于 **90%**，功率因数大于 **0.9**，并且总谐波失真 (THD) 小于 **20%**
- 可编程输出过压保护
- 过热关断
- **VCC** 欠压闭锁
- 带外露焊盘的 8 引脚超薄型小外形尺寸 (VSSOP) (表面贴装小外形尺寸 (MSOP)) 封装

### 应用范围

- 离线 TRIAC 可调光应用
- 离线不可调光灯
- 要求高效和尽可能低的物料清单 (BOM) 成本的灯
- 工业用和商用固态照明

### 说明

TPS92561 器件是一款升压控制器，此控制器用于采用高压、低电流 LED 的 LED 照明应用。在照明应用使用升压转换器的方法可生产出体积尽可能小的转换器，并且可实现 90% 以上的高效率。此器件包含一个具有固定偏移的电流感测比较器，从而实现简单滞后控制机制，此机制没有那些通常与升压转换器相关的环路补偿问题。集成过压保护 (OVP) 和 VCC 稳压器进一步简化了设计过程，并且减少了外部组件数量。

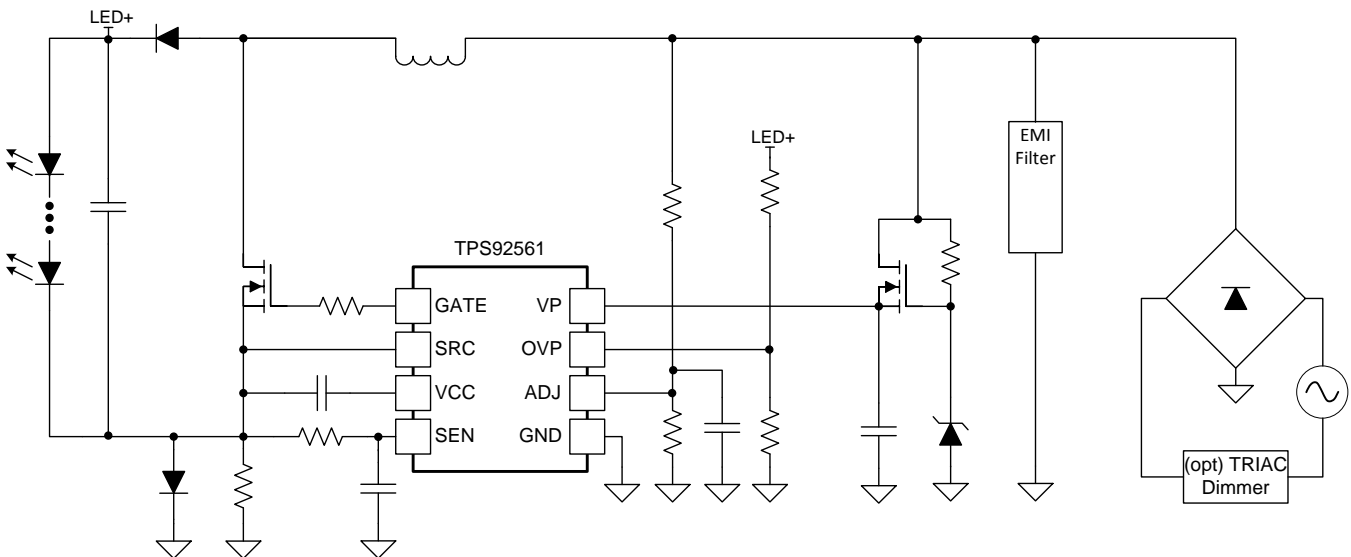


图 1. 典型应用电路原理图



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English Data Sheet: [SLVSCD1](#)



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### Absolute Maximum Ratings<sup>(1)</sup>

Over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Pin voltage range <sup>(2)</sup>	SRC, SEN, ADJ, OVP	-0.3	5.0	V
	VP	-1.0	45.0	
	VCC	-0.3	12.0	
ESD rating <sup>(3)</sup>	Human body model (HBM)	1.5		kV
T <sub>stg</sub>	Storage temperature range	-60	150	°C
T <sub>J</sub>	Junction temperature range	Internally Limited		

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to network ground terminal.
- (3) ESD testing is performed according to the respective JEDEC standard.

### Thermal Characteristics

Over operating free-air temperature range (unless otherwise noted)

THERMAL METRIC <sup>(1)</sup>		TPS92561	UNITS
		DGN (8 PINS)	
θ <sub>JA</sub>	Junction-to-ambient thermal resistance <sup>(2)</sup>	65.3	°C/W
θ <sub>JCtop</sub>	Junction-to-case (top) thermal resistance <sup>(3)</sup>	64.8	
θ <sub>JB</sub>	Junction-to-board thermal resistance <sup>(4)</sup>	44.8	
ψ <sub>JT</sub>	Junction-to-top characterization parameter <sup>(5)</sup>	3.9	
ψ <sub>JB</sub>	Junction-to-board characterization parameter <sup>(6)</sup>	44.6	
θ <sub>JCbot</sub>	Junction-to-case (bottom) thermal resistance <sup>(7)</sup>	13.2	

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, [SPRA953](#).
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specified JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, θ<sub>JT</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ<sub>JA</sub>, using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, θ<sub>JB</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ<sub>JA</sub>, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

### Recommended Operating Conditions

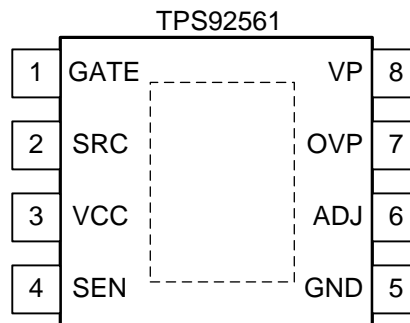
Over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
VP	Supply voltage	6.5		42	V
T <sub>J</sub>	Operating junction temperature	-40		125	°C

## Electrical Characteristics

 Over recommended operating conditions with  $-40^{\circ}\text{C} \leq T_J \leq 125^{\circ}\text{C}$ .  $V_{CC} = 12\text{ V}$ .  $C_{VCC} = 0.47\ \mu\text{F}$ 

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
<b>SUPPLY</b>						
$I_{IN}$	$V_P$ operating current	$6.5\text{ V} < V_{VP} < 42\text{ V}$	0.5	1.0	1.6	mA
<b>VCC Regulator</b>						
VCC	$V_{CC}$ regulated voltage	$I_{CC} \leq 10\text{ mA}$ $C_{VCC} = 0.47\ \mu\text{F}$ $12\text{ V} < V_{VP} < 42\text{ V}$	7.75	8.35	8.95	V
		$I_{CC} = 10\text{ mA}$ $C_{VCC} = 0.47\ \mu\text{F}$ $V_{VP} = 6.5\text{ V}$	5.42	5.92	6.42	
		$I_{CC} = 0\text{ mA}$ $C_{VCC} = 0.47\ \mu\text{F}$ $V_{VP} = 2\text{ V}$	2			
$I_{CC-LIM}$	$V_{CC}$ current limit	$V_{CC} = 0\text{ V}$ $6.5\text{ V} < V_{VP} < 42\text{ V}$	20	34	56	mA
$V_{CC-UVLO-UPTH}$	$V_{CC}$ UVLO rising threshold		5.00	5.44	5.85	V
$V_{CC-UVLO-LOTH}$	$V_{CC}$ UVLO falling threshold		4.68	5.07	5.46	V
<b>MOSFET Gate Driver</b>						
$V_{GATE-HIGH}$	Gate driver output high	With respect to SRC Sinking 100 mA from GATE Force $V_{CC} = 9.5\text{ V}$	8.00	8.71	9.41	V
$V_{GATE-LOW}$	Gate driver output low	With respect to SRC Sourcing 100 mA to GATE	10	180	350	mV
$t_{RISE}$	$V_{GATE}$ rise time	$C_{GATE} = 1\text{ nF}$ across GATE and SRC	37			ns
$t_{FALL}$	$V_{GATE}$ fall time	$C_{GATE} = 1\text{ nF}$ across GATE and SRC	30			
$t_{RISE-PG-DELAY}$	$V_{GATE}$ low-to-high propagation delay	$C_{GATE} = 1\text{ nF}$ across GATE and SRC	91			
$t_{FALL-PG-DELAY}$	$V_{GATE}$ high-to-low propagation delay	$C_{GATE} = 1\text{ nF}$ across GATE and SRC	112			
<b>Current Source at ADJ Pin</b>						
$I_{ADJ-STARTUP}$	Output current of ADJ pin at start-up	$V_{ADJ} < 90\text{ mV}$	14	20	26	$\mu\text{A}$
<b>Current Sense Amplifier</b>						
$V_{SEN-UPPER-TH}$	$V_{SEN}$ upper threshold over $V_{ADJ}$	$V_{SEN} - V_{ADJ}$ $V_{ADJ} = 0.2\text{ V}$ $V_{GATE}$ at falling edge	17.6	29.3	41	mV
$V_{SEN-LOWER-TH}$	$V_{SEN}$ lower threshold over $V_{ADJ}$	$V_{SEN} - V_{ADJ}$ $V_{ADJ} = 0.2\text{ V}$ $V_{GATE}$ at rising edge	-40.7	-29.1	-17.5	
$V_{SEN-HYS}$	$V_{SEN}$ hysteresis	$(V_{SEN-UPPER-TH} - V_{SEN-LOWER-TH})$	40.9	60.0	75.9	
$V_{SEN-OFFSET}$	$V_{SEN}$ offset with respect to $V_{ADJ}$	$(V_{SEN-UPPER-TH} + V_{SEN-LOWER-TH}) / 2$	-4.0	-0.1	4.0	
<b>Output Overvoltage Protection (OVP)</b>						
$V_{OVP-UPTH}$	Output overvoltage detection upper threshold	$V_{OVP}$ increasing, $V_{GATE}$ at falling edge	1.11	1.19	1.27	V
$V_{OVP-HYS}$	Output overvoltage detection hysteresis	$V_{OVP-UPTH} - V_{OVP-LOTH}$	15	44	80	mV
<b>Thermal Shutdown</b>						
$T_{SD}$	Thermal shutdown temperature	$T_J$ rising	165			$^{\circ}\text{C}$
$T_{SD-HYS}$	Thermal shutdown temperature hysteresis	$T_J$ falling	30			

**DEVICE INFORMATION**
**8-PIN VSSOP (MSOP) PACKAGE (EXPOSED PAD)  
(TOP VIEW)**

**Table 1. Terminal Functions**

PIN		DESCRIPTION	APPLICATION INFORMATION
NAME	NO.		
GATE	1	Gate driver output pin	Connect to the gate terminal of the low-side N-channel power FET. For off-line applications, use a gate resistance of $\geq 75 \Omega$ .
SRC	2	Gate driver return	Connect to the source terminal of the low-side, N-channel power FET. By connecting SRC to the FET source, switching current spikes are not passed through the sense resistor.
VCC	3	Gate driver power rail	Connect a 0.47- $\mu$ F minimum decoupling cap from this pin to SRC pin.
SEN	4	LED current sense pin	Current sense input. For off-line applications, connect to SEN and the current sensing resistor through an R-C filter with a time constant similar to the converter switching frequency.
GND	5	Ground	Connect to the system ground plane.
ADJ	6	LED current adjust pin	Converter reference. Can be connected to the converter rectified AC for high power factor, or to the LED output voltage for improved line regulation.
OVP	7	Overvoltage	Connect to resistor divider from VOUT (LED+) to detect overvoltage.
VP	8	Power supply of the integrated circuit (IC)	Connect to an appropriate voltage source to provide power for the IC. ( $VP \leq 42$ V) See <a href="#">Application Circuits</a> for example diagrams.
PowerPAD			Solder to printed circuit board (PCB) with or without thermal vias to enhance thermal performance. Although it can be left floating, TI recommends to connect the PowerPAD™ to GND.

Block Diagram

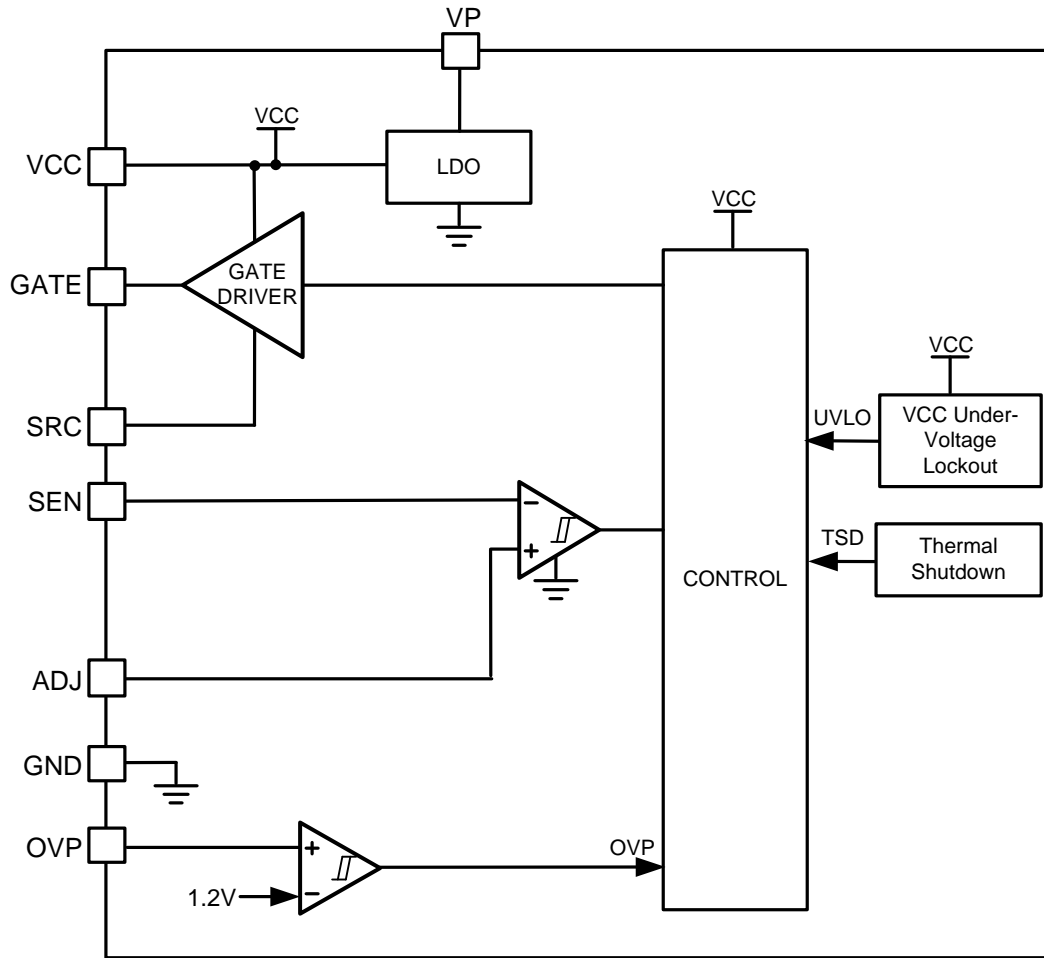


Figure 2. Functional Block Diagram

Typical Characteristics

$V_P = V_{P\_NOM} = 12\text{ V}$

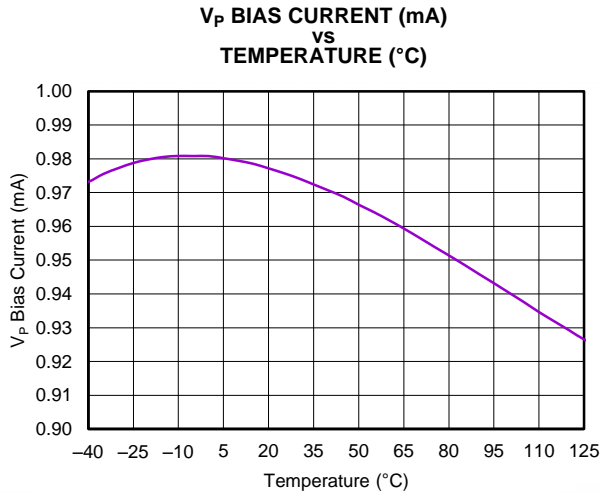


Figure 3. V<sub>P</sub> Operating Current (Non-Switching)

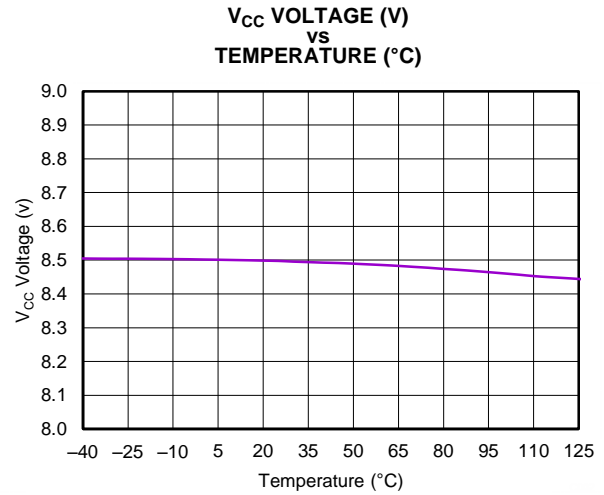


Figure 4. V<sub>CC</sub> Regulated Voltage

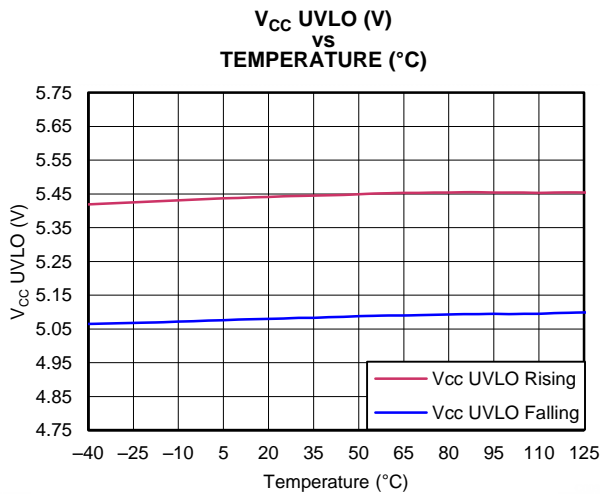


Figure 5. V<sub>CC</sub> UVLO Thresholds

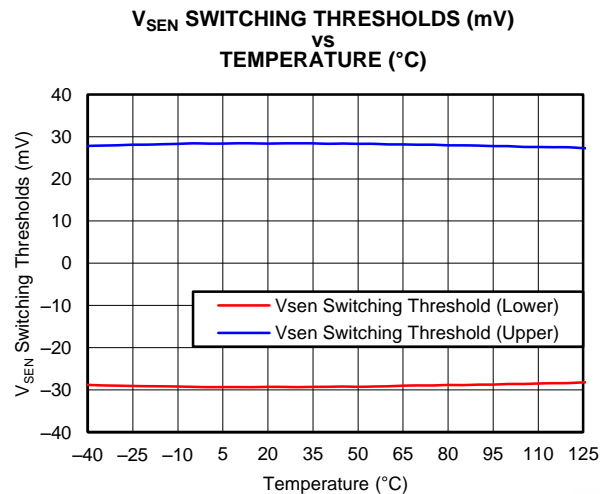
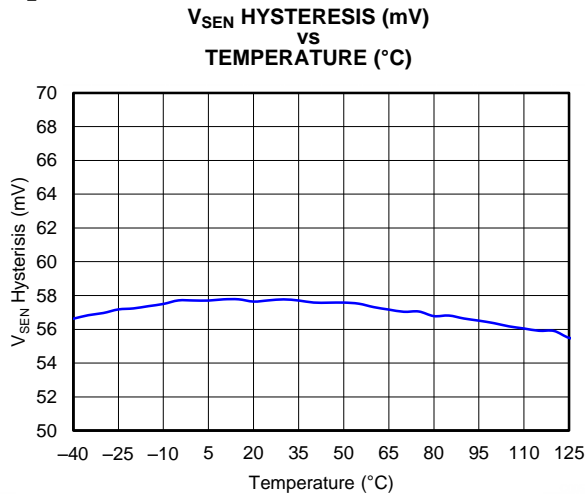
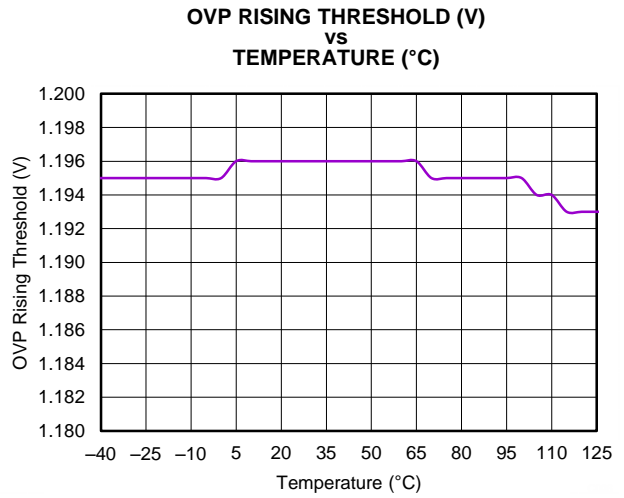


Figure 6. V<sub>SEN</sub> Switching Thresholds (mV)

$V_P = V_{P\_NOM} = 12\text{ V}$



**Figure 7. V<sub>SEN</sub> Hysteresis (mV)**



**Figure 8. OVP Threshold Voltages**

## APPLICATION INFORMATION

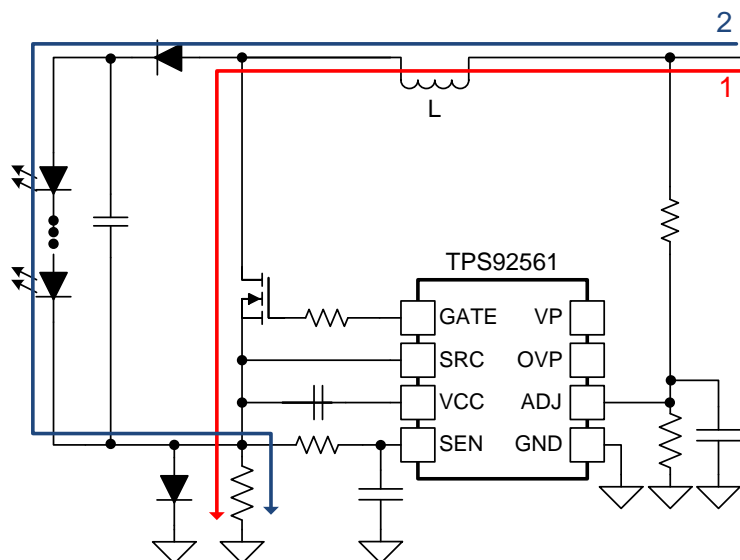
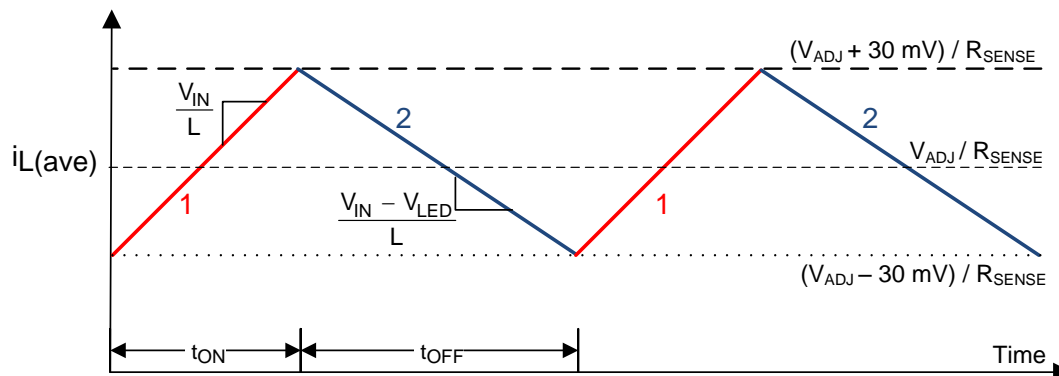
### Description

The TPS92561 device is a boost controller for phase cut dimmer compatible LED lighting applications. The device incorporates a current sense comparator with a fixed offset, allowing the construction of a hysteretic, off-line converter suitable for driving LEDs in a wide variety of applications.

The inductor peak-to-peak current ripple follows the device reference, the ADJ pin voltage ( $V_{ADJ}$ ), and is bounded by the SEN pin hysteresis ( $V_{SEN-HYS}$ ). By using a voltage divider from the rectified AC voltage, the inductor current can be made to follow the line closely and create conversions which result in high power factor and low THD. Boost converters also have an advantage when TRIAC dimming because of their inherent ability to draw continuous current from the line. This eliminates the need for additional hold current circuitry as the converter itself can draw power until the zero crossing point is reached. The continuous input current of a boost also reduces the input EMI filter requirements.

### Basics of Operation

The main switch is turned on and off when the SEN comparator reaches trip points in a window around the ADJ reference. In cycle 1, the main switch is on until the current reaches the turn off threshold. In cycle 2, the switch is kept off until the turn on threshold is reached. In Figure 9,  $V_{SEN-UPPER\_TH}$  and  $V_{SEN-LOWER\_TH}$  are assumed to be their typical value of 30 mV.

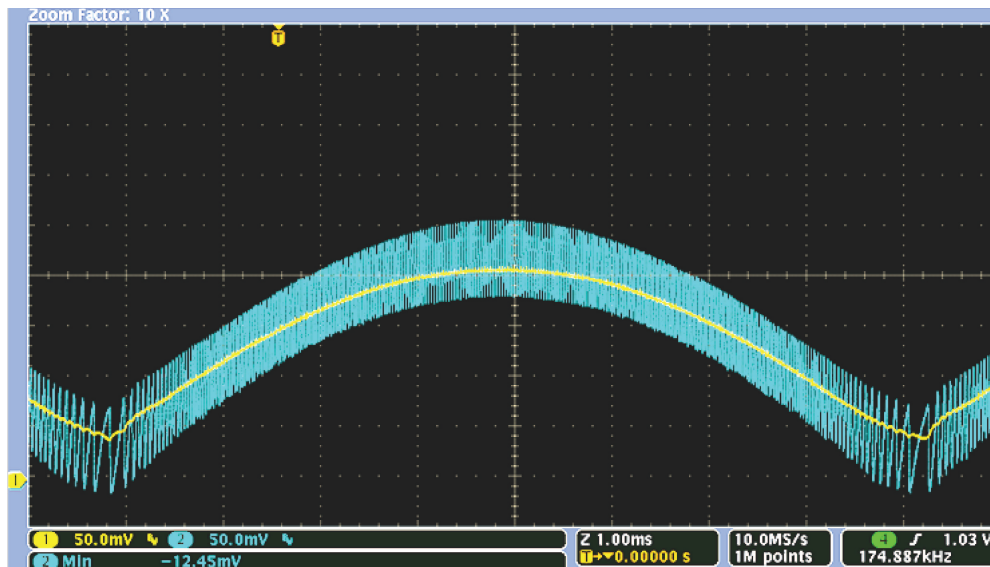


**Figure 9. Basics of Hysteretic Boost Operation**



## Sample Scope Capture

The main inductor current varies in a window around the ADJ reference voltage:



**Figure 10. TPS92561 Operation Waveform (1 ms/div)**  
Yellow: ADJ Voltage (50 mV/div) Blue: R<sub>SENSE</sub> Voltage (50 mV/div)

## VCC Bias Supply and Start-Up

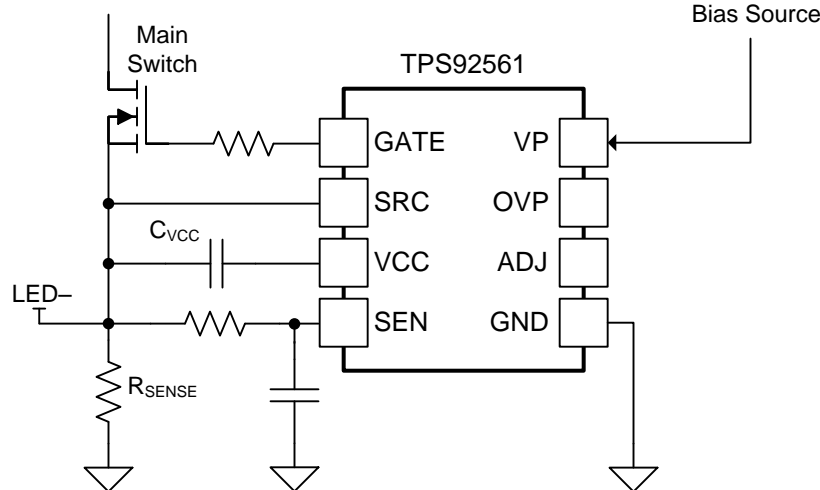
The TPS92561 device can be configured to obtain bias power in several different configurations: AUX winding from the main inductor (see [Figure 15](#)), a linear regulator from the input rectified AC (see [Figure 16](#)), or a linear regulator from the output LED voltage (see [Figure 17](#)). A linear regulator can be constructed from a resistor, a Zener diode, and a N-Channel MOSFET. Each configuration has benefits and trade-offs.

**Table 2. VCC Bias Power Configurations**

Bias Configuration	Description
Coupled inductor bias with linear regulator start-up (see <a href="#">Figure 15</a> )	Highest efficiency bias choice
	Requires a custom magnetic, which can range in cost similar to an off-the-shelf single coil inductor
	Method to start the TPS92561 device (linear) still required, however, can be undersized for start-up condition only. VCC <sub>UVLO</sub> has not been engineered to support resistive start-up methods.
Linear regulator from output (see <a href="#">Figure 16</a> )	Lowest efficiency bias choice because output voltage is higher than input
	Ensures fast output turn off due to bias draining output capacitor
	Aids dimming performance under deep dimming, a stable bias is always available
	Lower capacitance value required at VP pin, output capacitor is doubling as VP capacitor
Linear regulator from input (see <a href="#">Figure 17</a> )	Can be supplemented with charge pump bias circuit to achieve higher efficiency
	Better efficiency performance than linear regulator derived from output
	Higher VP capacitor value required

## VCC and VP Connection

A bias voltage with a maximum of 42 V is connected to the VP pin to supply the internal 8.3 V (typical) VCC linear regulator. This voltage is also used to drive the main FET gate. Use a FET with a gate threshold at least 750 mV below the VCC voltage. The VCC capacitor ground must be placed at the SEN pin. This ensures the SEN voltage is free of switching spikes that occur at the edge of each switching cycle.



**Figure 11. TPS92561 Bias, SRC, and C<sub>VCC</sub> Connection**

## Output Current Control (ADJ, SEN)

The TPS92561 power stage design follows two rules:

1. Output current is determined by the ADJ reference voltage, the sense resistor selected, and the converter operating points,  $V_{IN}$  and  $V_{LED}$ .
2. Output frequency is determined by the inductance value and the SEN pin hysteresis  $V_{SEN}$ . For off-line applications, the effective hysteresis must be increased using an R-C filter on the SEN pin.

Because the TPS92561 device does not have leading edge blanking, the SEN pin filter must be used to obtain consistent operation. The SEN pin filter is typically set using an R-C with a corner frequency close to the desired switching frequency. Leading edge blanking was not implemented to allow high-frequency operation in other non-off-line applications.

At start up ( $V_{ADJ} < 90$  mV) a small current is supplied to the  $V_{ADJ}$  divider to ensure a reference is available to begin converter switching. When the ADJ voltage is above 90 mV, the current source is shut off.

## Setting the Output Current

Using the desired ADJ reference voltage, the input current can be calculated based on:

$$I_{in} = \frac{V_{ADJ}}{R_{SENSE}}$$

where  $V_{ADJ}$  can be DC, rectified AC derived, or other source. (1)

If  $V_{ADJ}$  is derived from a voltage divider from the input rectified AC, we can solve for the R9 resistor divider value based on, for example, a  $V_{ADJ}$  voltage of 150 mV, an R17 value of 374  $\Omega$ , and the average value of the sine wave:

$$R9 = \frac{(V_{IN_{RMS}} \times 0.9 \times R17)}{V_{ADJ}} - R17$$
(2)

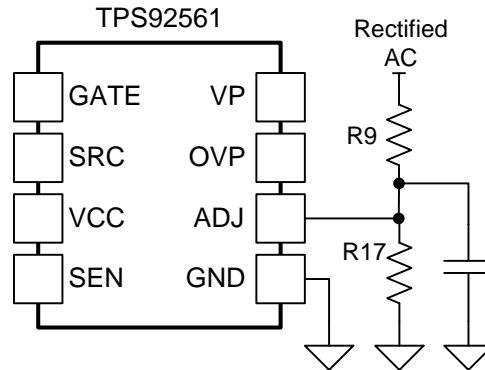


Figure 12. TPS92561 ADJ Connection

To find the  $R_{SENSE}$  value, where  $\eta$  is the converter efficiency, assume 0.9.

$$R_{SENSE} = \frac{V_{IN-RMS} \times V_{ADJ} \times \eta}{V_{LED} \times I_{LED}} \quad (3)$$

### Selecting an Inductance

The TPS92561 device is hysteretic. Therefore, switching transitions are based on the sensed current in the inductor. There is no direct control of the switching frequency other than the relationship of the comparator hysteresis to the inductor ripple. A typical switching frequency of an off-line converter using a rectified AC injected reference could vary up to 50 kHz over a line cycle. This creates a spread-spectrum effect and helps reduced conducted EMI.

A typical line injected (using a divided down rectified AC as the reference) hysteretic boost converter reaches the peak switching frequency when  $V_{LED} = 2 \times V_{RECTIFIED\ AC}$ , or when the duty cycle  $D = 0.5$ . We call this operating point  $V_{IN-FSW-PK}$ . Use this voltage as the typical operating point for the design equations. Solve for the  $V_{IN-FSW-PK}$  term based on:

$$\frac{V_{LED}}{V_{IN-FSW-PK}} = \frac{1}{1-D} \quad \text{or} \quad V_{IN-FSW-PK} = \frac{V_{LED}}{2} \quad (4)$$

Select the approximate highest desired frequency (for example,  $f_{SW-PK}$  of 65 kHz could be used), then design the SEN pin filter with corner frequency equal to  $f_{SW-PK}$ . The filter and the internal hysteresis define the inductor ripple for a given inductance. This has the effect of increasing the SEN pin hysteresis  $V_{SEN-HYS-2}$  to approximately 140 mV. Select a C12 value between 1000 and 4700 pF. Solve for the resistor R12 in the filter based on:

$$R_{12} = \frac{1}{2\pi \times f_{SW-PK} \times C_{12}} \quad (5)$$

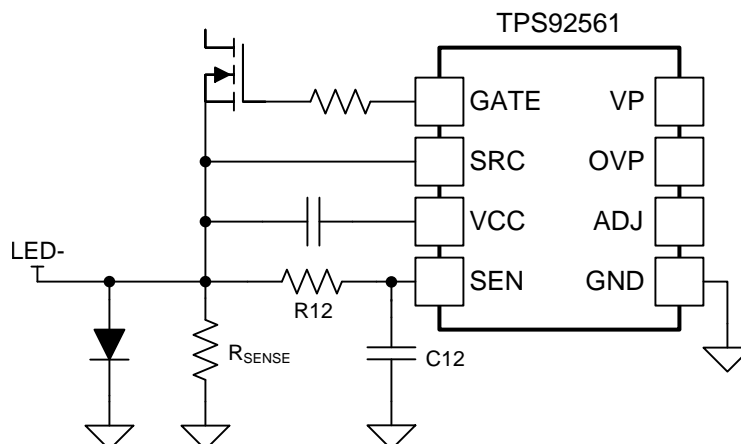


Figure 13. Current Sense

With the effective hysteresis, calculate the inductor peak-to-peak,  $\Delta i_{L-PP}$  ripple current using:

$$\Delta i_{L-PP} = \frac{V_{SEN-HYS-2}}{R_{SENSE}} \quad (6)$$

To find the converter inductance, L, substitute into:

$$L = \frac{V_{IN-FSW-PK} \times D \times \left( \frac{1}{f_{SW-PK}} \right)}{\Delta i_{L-PP}} \quad (7)$$

To further aid in the converter design, see the TPS92561 [design tool](#), TI literature number *SLUC517*.

### Important Design Consideration: Diode in Parallel With Sense Resistance

**Figure 13** shows a diode in use in parallel with the  $R_{SENSE}$  resistor. The diode clamps the SEN pin voltage when the boost converter is first powered up. Because a boost converter utilizes a diode connected to the output, the output capacitor is charged immediately when power is applied.

#### CAUTION

The current charging the output capacitor when  $V_{IN}$  is applied flows through the sense resistors, and if it is not clamped by the diode, can exceed the TPS92561 SEN pin rating, which may damage the device.

### Gate Driver Operation

An additional aid to converter operation and radiated EMI is to slow the main FET switching speed. This can be accomplished by adding a resistor in series with the FET gate. A fast turn off diode across the resistor could also be implemented to improve efficiency. For off-line designs, use a gate resistance value  $\geq 75 \Omega$ .

As in all power converters grounding and layout are key considerations. Give careful attention to the layout of the sense resistors, GND pin, VCC, and SRC connections, as well as the FET Gate and Source connections. All should follow short and low-inductance paths. For examples, see the TPS92561 EVM [User's Guide](#), *SLUUAU9*.

### Overcurrent Protection

The TPS92561 device inherently limits the main switch current, but cannot implement output short circuit protection because of the converter (boost) topology. To implement LED short-circuit protection in a boost converter requires a blocking switch or other means to open the path to the output, which adds significant cost and complexity to the solution and is not commonly used. An input fuse should be used as output overcurrent protection.

### Overvoltage Protection (OVP)

Overvoltage protection is implemented using a resistor voltage divider to the output. Note that the output voltage is high ( $> 200 \text{ V}$ ) so the resistor divider should contain a high ( $> 1 \text{ M}\Omega$ ) value. Also use a small cap on OVP.

First pick a value for R18, for example  $1.6 \text{ M}\Omega$  and select the desired overvoltage protection voltage  $V_{OVP}$ . Using the  $V_{OVP-UPTH}$  value ( $1.19 \text{ V}$ , typical) the trip point can then be computed using:

$$R19 = \frac{R18 \times V_{OVP-UPTH}}{V_{OVP} - V_{OVP-UPTH}} \quad (8)$$

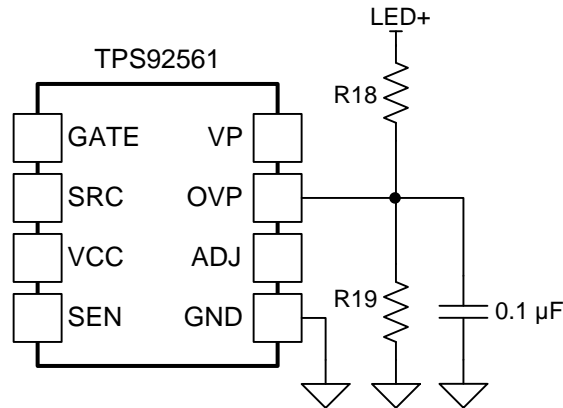


Figure 14. Overvoltage Protection Circuit

When the OVP trip point is reached the converter shuts off until the OVP voltage drops below the level controlled by the OVP hysteresis,  $V_{OVP-HYS}$  (44 mV, typical). After OVP is reached, switching begins again when  $V_{LED}$  falls to the restart voltage (one  $V_{OVP-HYS}$  term ignored):

$$V_{OVP\_RESTART} = V_{OVP} - \left( \frac{V_{OVP-HYS}}{R19} \right) R18 \quad (9)$$

### Output Bulk Capacitor

The required output bulk capacitor,  $C_{BULK}$ , stores energy during the input voltage zero crossing interval and limits the twice the line frequency ripple component flowing through the LEDs. The following equation describes the calculation of the output capacitor value:

$$C_{BULK} \geq \frac{P_{IN}}{4\pi \times f_L \times R_{LED} \times V_{LED} \times I_{LED(ripple)}}$$

where

- $R_{LED}$  is the dynamic resistance of LED string
  - $I_{LED(ripple)}$  is the peak-to-peak LED ripple current
  - $f_L$  is line frequency
- (10)

$R_{LED}$  is found by computing the difference in LED forward voltage divided by the difference in LED current for a given LED using the manufacturer's  $V_F$  versus  $I_F$  curve. For more details, see [Application Note 1656](#).

In typical applications, the solution size becomes a limiting factor and dictates the maximum dimensions of the bulk capacitor. When selecting an electrolytic capacitor, manufacturer recommended de-rating factors should be applied based on the worst case capacitor ripple current, output voltage, and operating temperature to achieve the desired operating lifetime.

### Phase Dimming

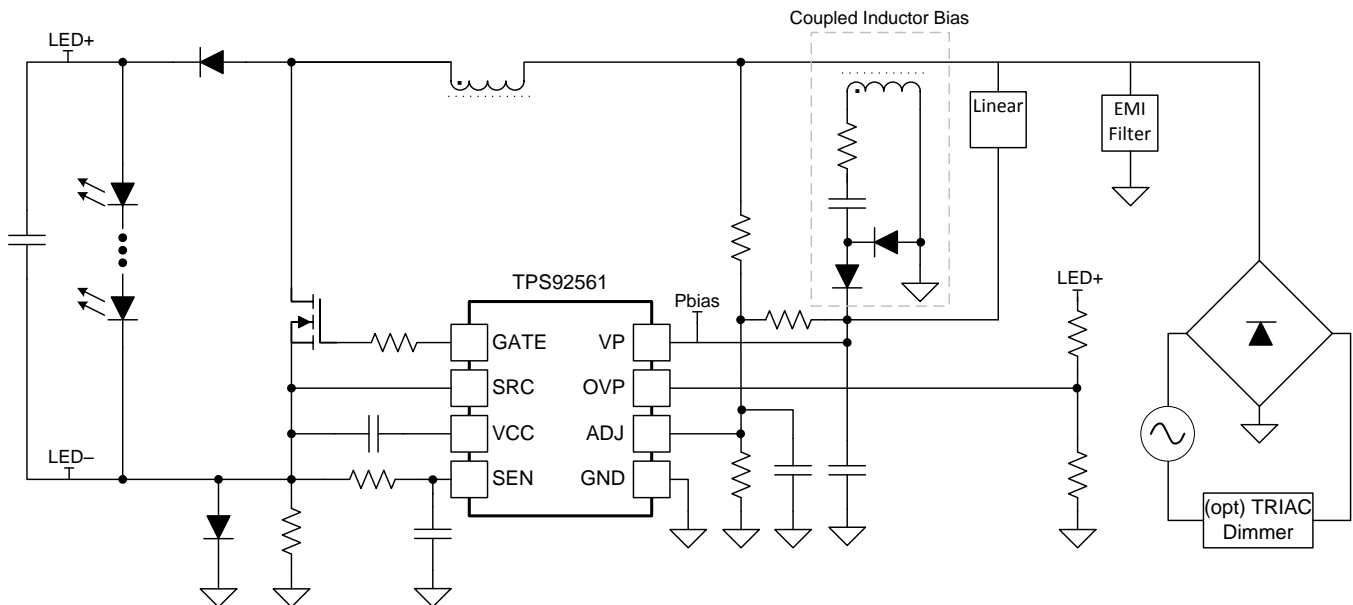
After following the design procedure for a TPS92561 non-dimming design, the creation of a TRIAC dimmer compatible design only requires the addition of an input snubber (R-C), as shown in [Figure 17](#). Ideally, a capacitor value of 3x the input filter capacitance would be implemented to ensure sufficient damping of the input filter resonance. However, capacitance values as low as 2x tested successfully. If the input voltage is used to provide the converter reference, dimming occurs naturally with the decreasing ADJ set point and decreased power transfer due to shorter line-cycle conduction times.

## Application Circuits

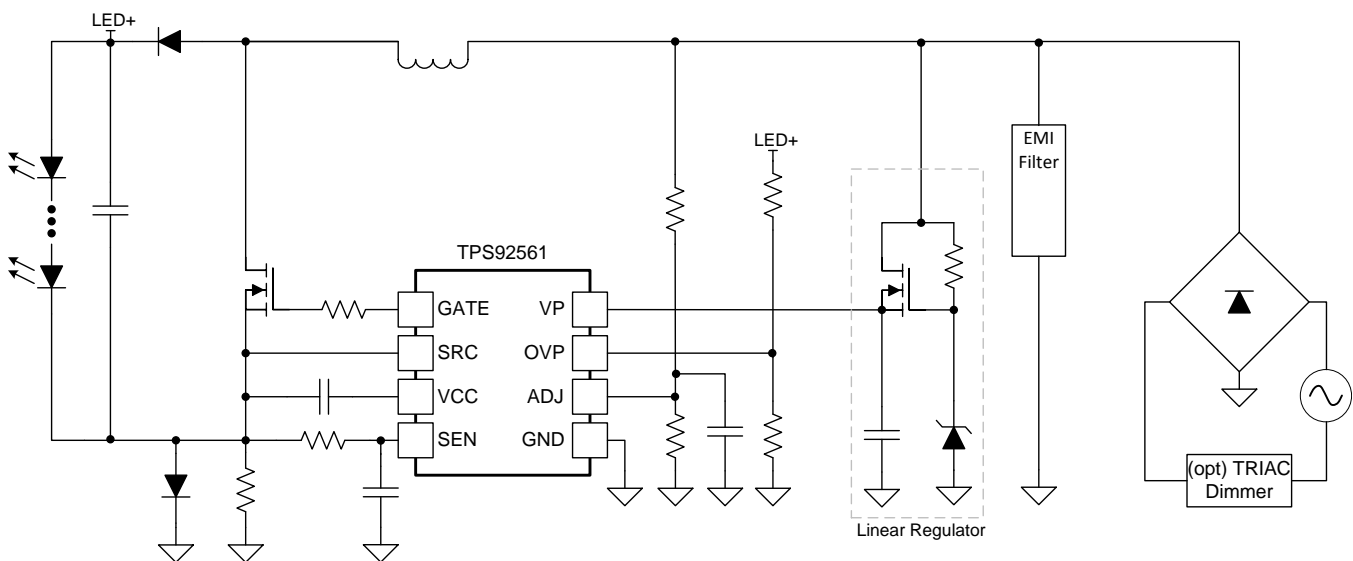
Target LED lamp applications include:

- A-15, A-19, A-21, A-23
- R-20, R-25, R-27, R-30, R-40
- PS-25, PS-30, PS-35
- BR-30, BR-38, BR-40
- PAR-20, PAR-30, PAR-30L
- MR-16, GU-10
- G-25, G-30, G-40

Applications also include: fluorescent replacement, recessed (canister) type lighting replacement, and new LED-specific lighting form factors.



**Figure 15. Offline Boost Configuration With Auxiliary Winding and Linear Regulator for Start-Up**



**Figure 16. Offline Boost With Linear Regulator from Input Rectified AC**

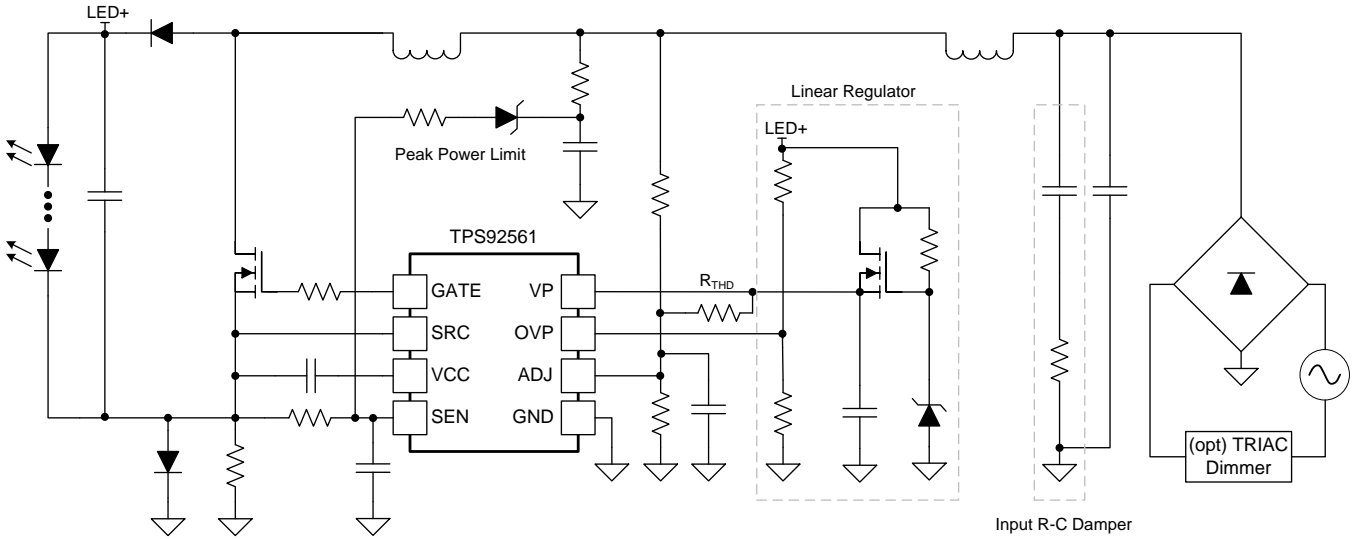


Figure 17. Offline Boost With Linear Regulator from  $V_{LED+}$ , THD Improvement Resistor, Peak Power Limit Circuit, EMI Filter, and Snubber for TRIAC Dimming

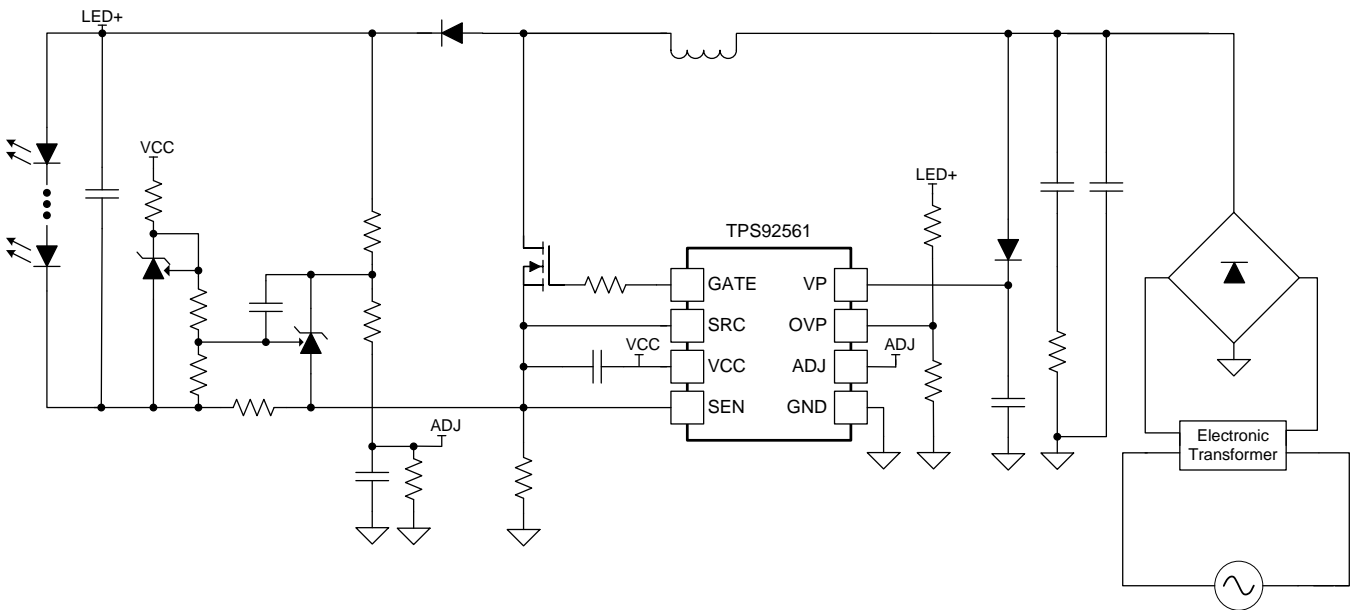


Figure 18. Closed-Loop Regulated E-Transformer Compatible, Non-TRIAC Dimmable Boost for AR111 and MR16 Lamps

## 修订历史记录

<b>Changes from Original (December 2013) to Revision A</b>	<b>Page</b>
<ul style="list-style-type: none"><li>Updated figure to add AR111 lamps for closed-loop regulated e-transformer compatible, non-TRIAC dimmable boost for AR111 and MR16 lamps .....</li></ul>	<b>15</b>

<b>Changes from Revision A (December 2013) to Revision B</b>	<b>Page</b>
<ul style="list-style-type: none"><li>已删除产品预览条 .....</li></ul>	<b>1</b>



**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS92561DGN	ACTIVE	HVSSOP	DGN	8	80	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	92561	<a href="#">Samples</a>
TPS92561DGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	92561	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS92561DGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS92561DGNR	HVSSOP	DGN	8	2500	366.0	364.0	50.0

**TUBE**


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
TPS92561DGN	DGN	HVSSOP	8	80	330	6.55	500	2.88

## GENERIC PACKAGE VIEW

**DGN 8**

**PowerPAD VSSOP - 1.1 mm max height**

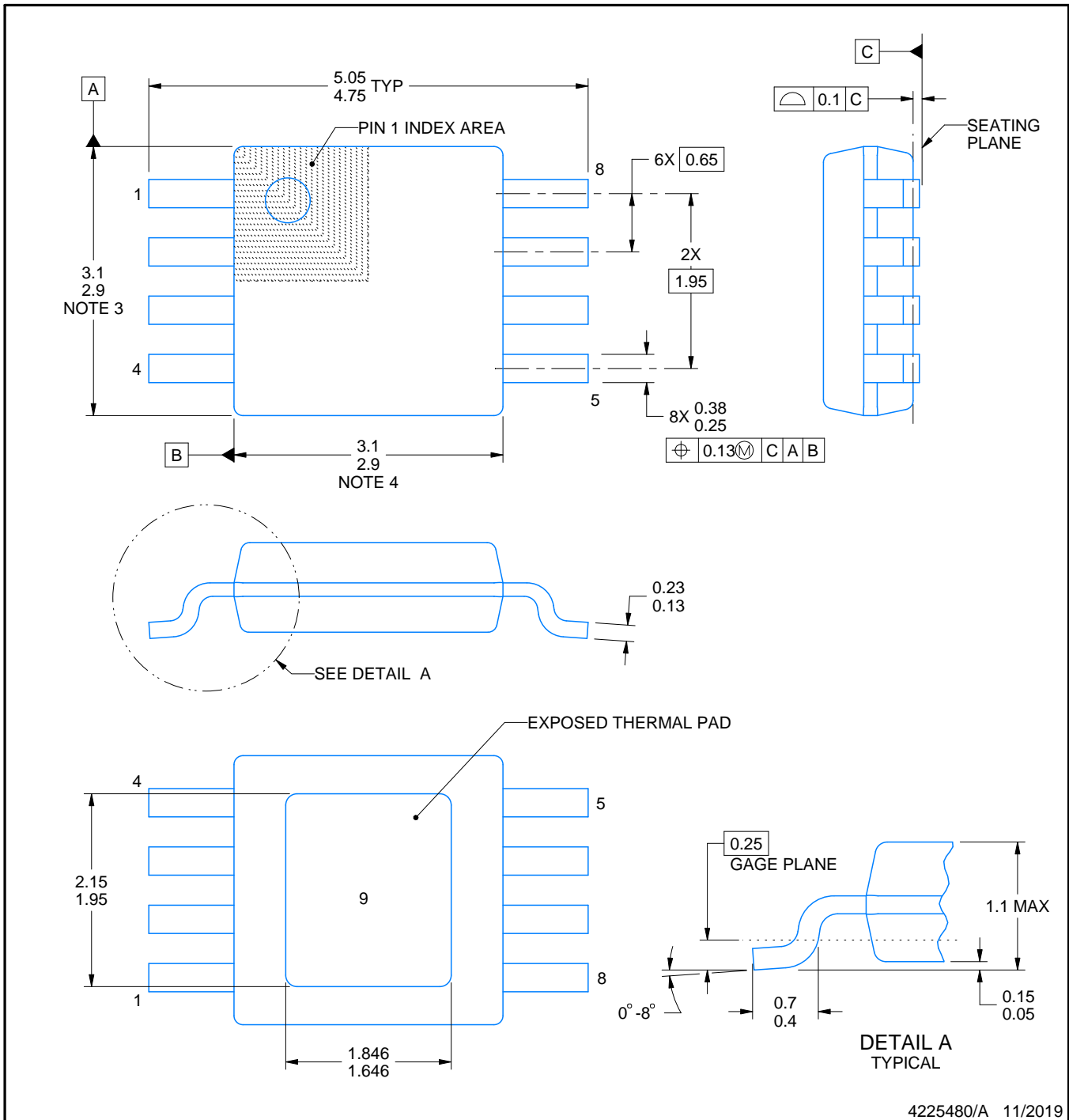
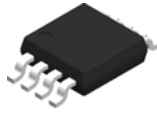
3 x 3, 0.65 mm pitch

SMALL OUTLINE PACKAGE

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



4225482/A



4225480/A 11/2019

PowerPAD is a trademark of Texas Instruments.

NOTES:

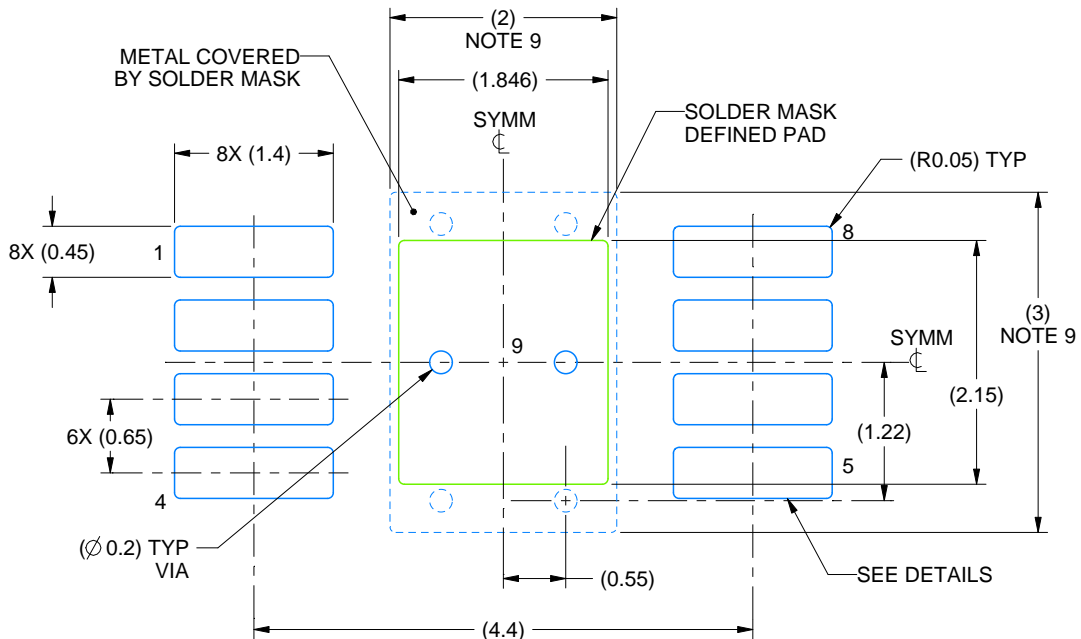
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

# EXAMPLE BOARD LAYOUT

DGN0008G

PowerPAD™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 15X



SOLDER MASK DETAILS

4225480/A 11/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

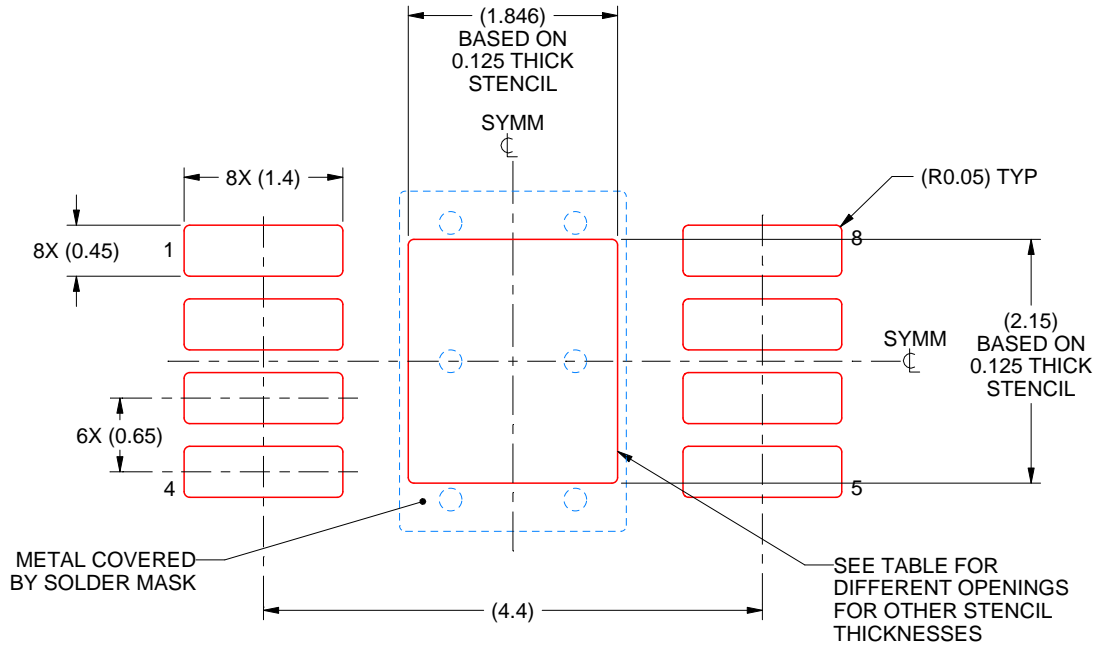


# EXAMPLE STENCIL DESIGN

DGN0008G

PowerPAD™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



**SOLDER PASTE EXAMPLE**  
 EXPOSED PAD 9:  
 100% PRINTED SOLDER COVERAGE BY AREA  
 SCALE: 15X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	2.06 X 2.40
0.125	1.846 X 2.15 (SHOWN)
0.15	1.69 X 1.96
0.175	1.56 X 1.82

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NOTES: (continued)

10. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
11. Board assembly site may have different recommendations for stencil design.

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